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 $R - S i H_n X_{1-n}$ 

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APPLICANT: IBIDEN COLTD;

INVENTOR: AMINO TOSHIKAZU;

ChHznez

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TITLE

: PRODUCTION OF BETA TYPE

SILICON CARBIDE POWDER

ABSTRACT: PURPOSE: To obtain high-purity β type SiC fine powder inexpensively and efficiently, by thermally decomposing an organosilicon compound with a specific gas and heat-treating the obtained fine powder.

> CONSTITUTION: An organosilicon compound shown by formula I (R is CH<sub>3</sub> or C<sub>2</sub>H<sub>5</sub>; X is CI; n is 1~2) and a carrier gas containing ≥95wt.% hydrocarbon gas shown by formula II such as methane are introduced into a reaction system and chemically reacted in a gas phase at 800~1,200°C to give fine powder. Then the powder is heat-treated at 1,200~2,200°C to produce β type SiC fine powder having ≥95wt.% purity and 1~6m<sup>2</sup>/g specific surface area.

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